

PBSS8110D

100 V, 1 A NPN low V_{CEsat} (BISS) transistor

Rev. 01 — 23 April 2004

Product data sheet

1. Product profile

1.1 General description

NPN low V_{CEsat} transistor in a plastic SOT457 (SC-74) package.

1.2 Features

- SOT457 package
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High efficiency, leading to less heat generation.

1.3 Applications

- Major application segments:
 - ◆ Automotive 42 V power
 - ◆ Telecom infrastructure
 - ◆ Industrial.
- DC-to-DC converter
- Peripheral driver
 - ◆ Driver in low supply voltage applications (e.g. lamps and LEDs)
 - ◆ Inductive load drivers (e.g. relays, buzzers and motors).

1.4 Quick reference data

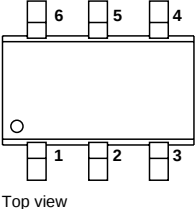
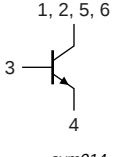
Table 1: Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage		-	-	100	V
I_C	collector current (DC)		-	-	1	A
I_{CM}	peak collector current		-	-	3	A
R_{CEsat}	equivalent on-resistance		-	-	200	m Ω

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2. Pinning information

Table 2: Discrete pinning

Pin	Description	Simplified outline	Symbol
1, 2, 5, 6	collector	 Top view	 sym014
3	base		
4	emitter		

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
PBSS8110D	-	plastic surface mounted package; 6 leads	SOT457

4. Marking

Table 4: Marking

Type number	Marking code ^[1]
PBSS8110D	A8

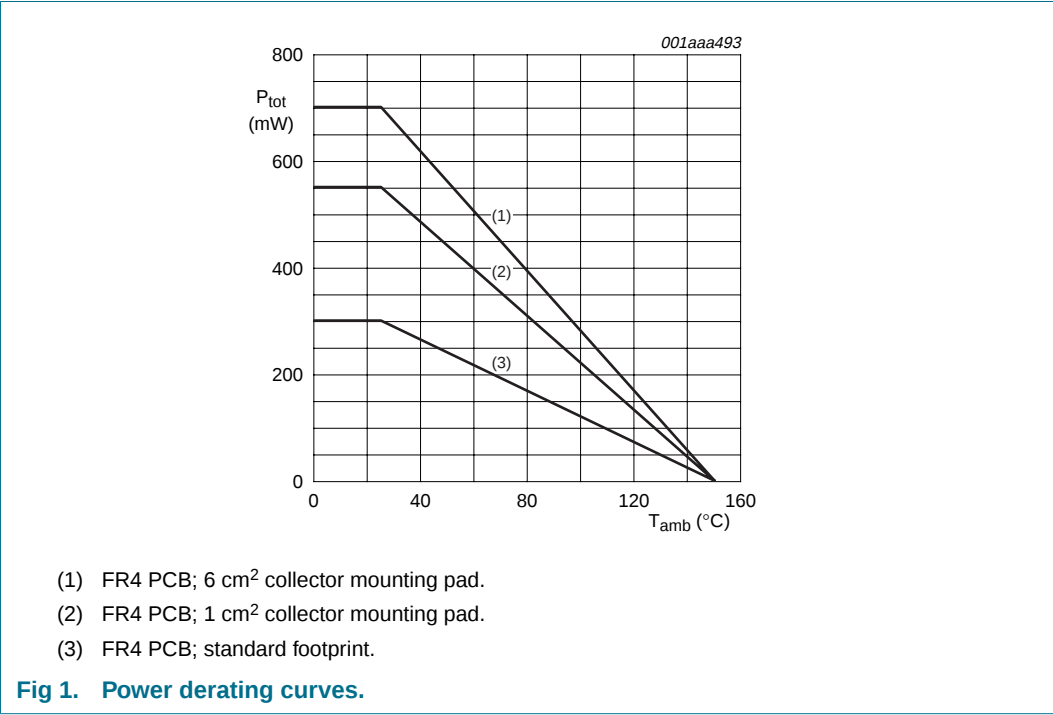
[1] Made in Malaysia.

5. Limiting values

Table 5: Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	120	V
V _{CEO}	collector-emitter voltage	open base	-	100	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
I _{CM}	peak collector current	T _{j(max)}	-	3	A
I _C	continuous collector current		-	1	A
I _B	continuous base current		-	0.3	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	300	mW
			[2] -	550	mW
			[3] -	700	mW
T _j	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		−65	+150	°C
T _{stg}	storage temperature		−65	+150	°C

- [1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, standard footprint.
- [2] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, 1 cm² collector mounting pad.
- [3] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, 6 cm² collector mounting pad.

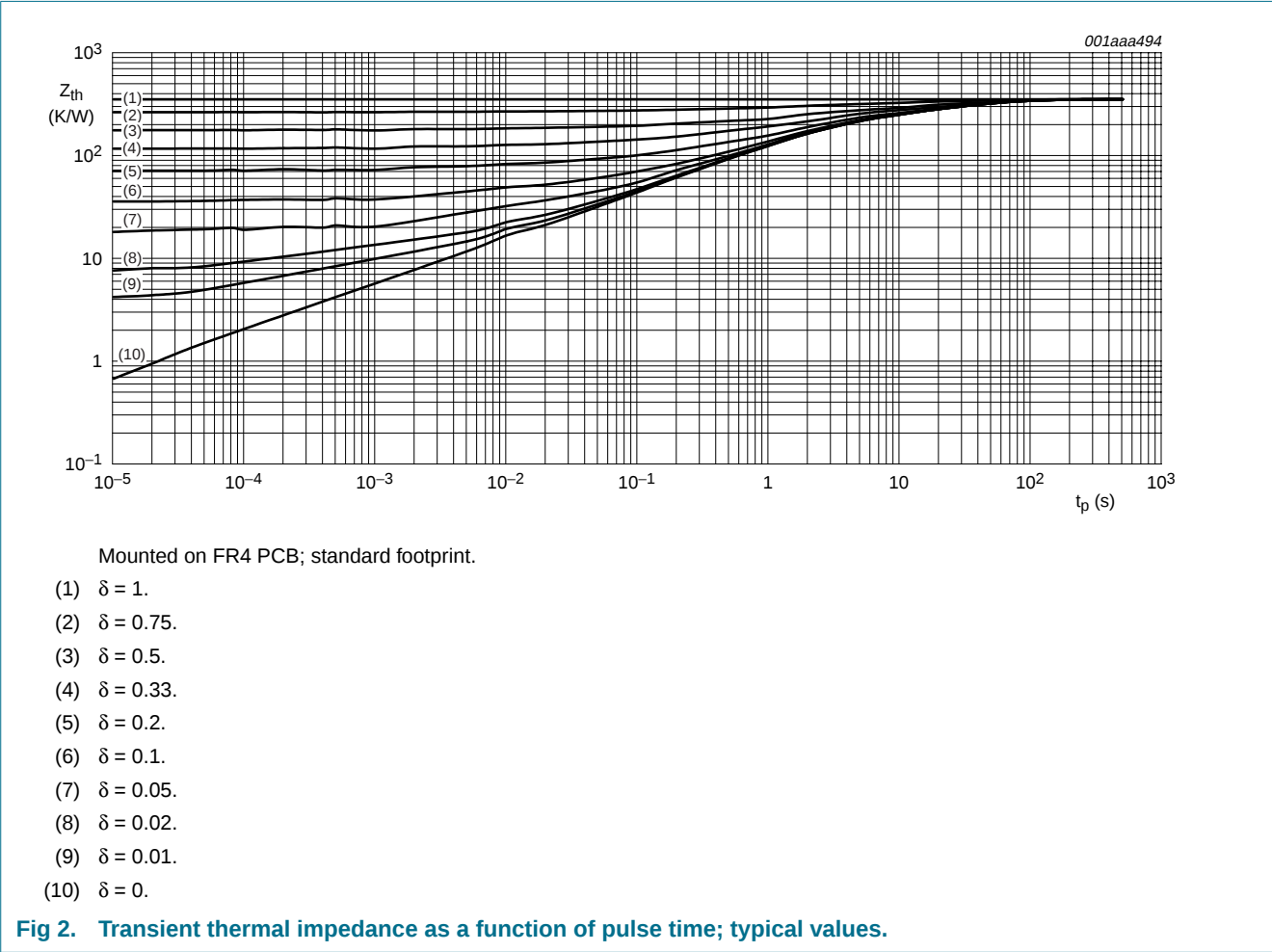


6. Thermal characteristics

Table 6: Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] 416	K/W
			[2] 227	K/W
			[3] 178	K/W
$R_{th(j-s)}$	thermal resistance from junction to soldering point	in free air	[1] 83	K/W

- [1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, standard footprint.
[2] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, 1 cm² collector mounting pad.
[3] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, 6 cm² collector mounting pad.



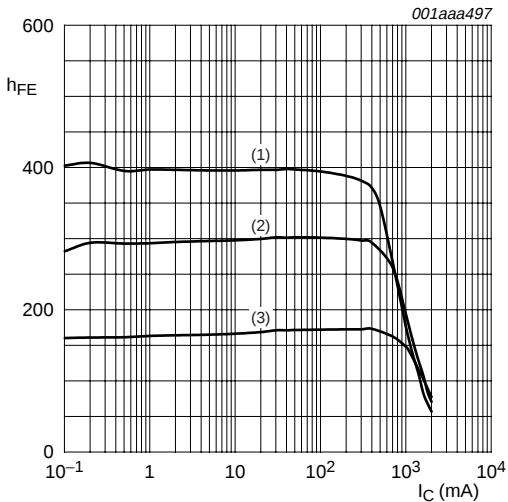
7. Characteristics

Table 7: Characteristics

$T_j = 25^\circ\text{C}$ unless otherwise specified.

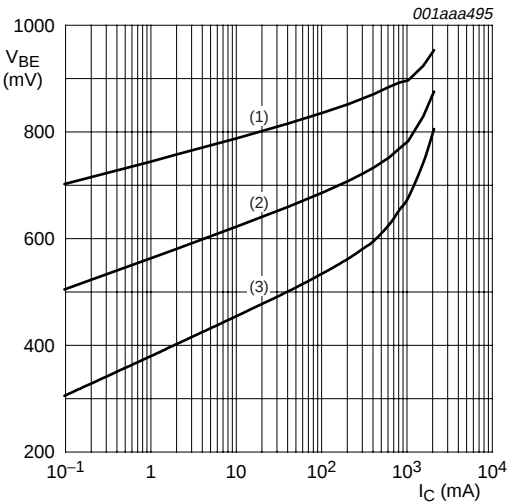
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = 80\text{ V}; I_E = 0\text{ A}$	-	-	100	nA
		$V_{CB} = 80\text{ V}; I_E = 0\text{ A}; T_j = 150^\circ\text{C}$	-	-	50	μA
I_{CES}	collector-emitter cut-off current	$V_{CE} = 80\text{ V}; V_{BE} = 0\text{ V}$	-	-	100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 4\text{ V}; I_C = 0\text{ A}$	-	-	100	nA
h_{FE}	DC current gain	$V_{CE} = 10\text{ V}; I_C = 1\text{ mA}$	150	-	-	
		$V_{CE} = 10\text{ V}; I_C = 250\text{ mA}$	150	-	500	
		$V_{CE} = 10\text{ V}; I_C = 0.5\text{ A}$ [1]	100	-	-	
		$V_{CE} = 10\text{ V}; I_C = 1\text{ A}$ [1]	80	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 10\text{ mA}$	-	-	40	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	-	-	120	mV
		$I_C = 1\text{ A}; I_B = 100\text{ mA}$	-	-	200	mV
R_{CEsat}	equivalent on-resistance	$I_C = 1\text{ A}; I_B = 100\text{ mA}$ [1]	-	160	200	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 100\text{ mA}$	-	-	1.05	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 10\text{ V}; I_C = 1\text{ A}$	-	-	0.9	V
f_T	transition frequency	$V_{CE} = 10\text{ V}; I_C = 50\text{ mA}; f = 100\text{ MHz}$	100	-	-	MHz
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_C = 0\text{ A}; f = 1\text{ MHz}$	-	-	7.5	pF

[1] Pulse test $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.



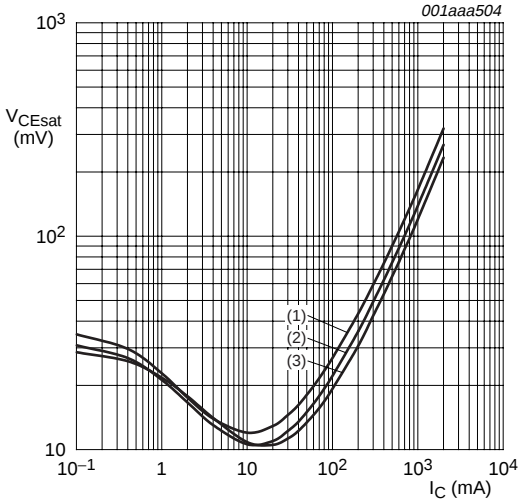
- $V_{CE} = 10\text{ V.}$
- (1) $T_{amb} = 100\text{ °C.}$
 - (2) $T_{amb} = 25\text{ °C.}$
 - (3) $T_{amb} = -55\text{ °C.}$

Fig 3. DC current gain as a function of collector current; typical values.



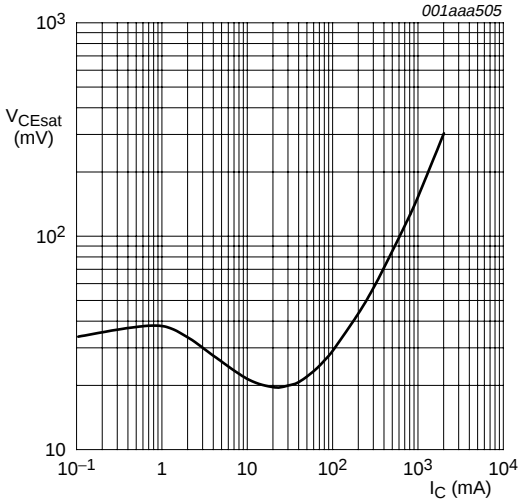
- $V_{CE} = 10\text{ V.}$
- (1) $T_{amb} = -55\text{ °C.}$
 - (2) $T_{amb} = 25\text{ °C.}$
 - (3) $T_{amb} = 100\text{ °C.}$

Fig 4. Base-emitter voltage as a function of collector current; typical values.



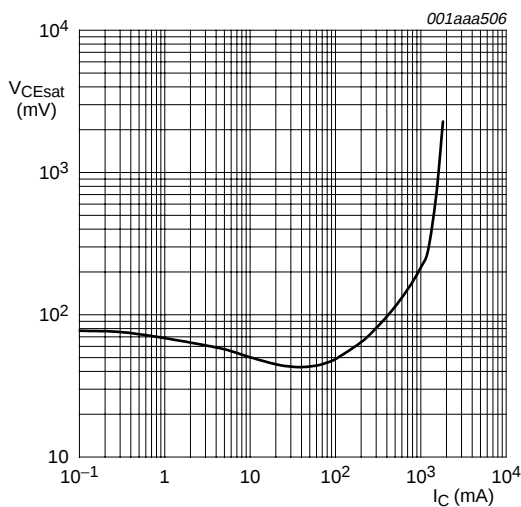
- $I_C/I_B = 10.$
- (1) $T_{amb} = 100\text{ °C.}$
 - (2) $T_{amb} = 25\text{ °C.}$
 - (3) $T_{amb} = -55\text{ °C.}$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values.



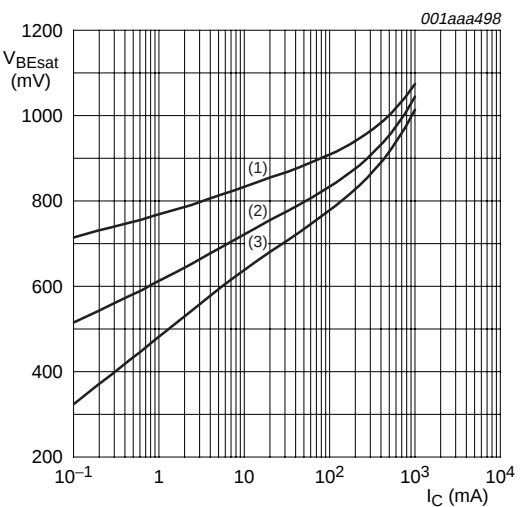
- $I_C/I_B = 20; T_{amb} = 25\text{ °C.}$

Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values.



$I_C/I_B = 50$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

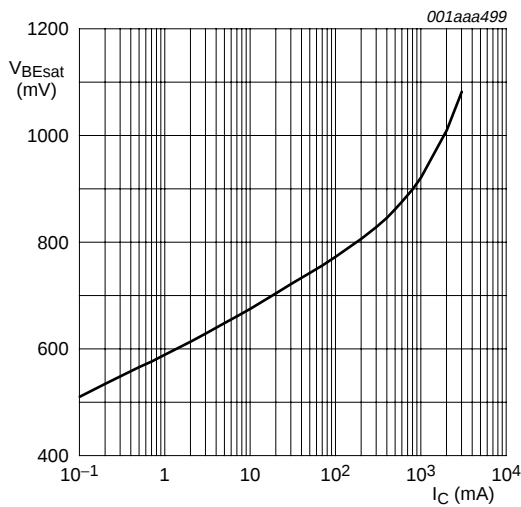
Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values.



$I_C/I_B = 10$.

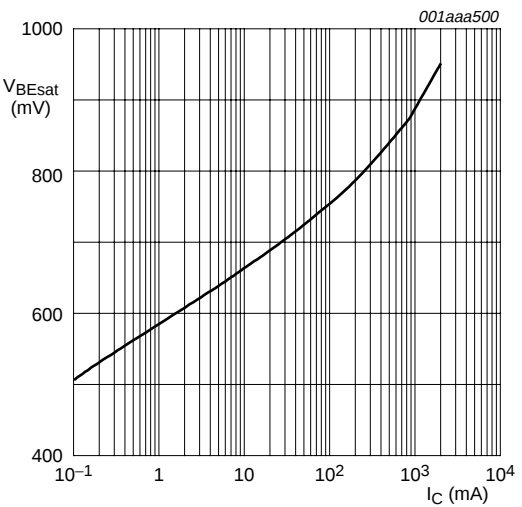
- (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 100\text{ }^{\circ}\text{C}$.

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values.



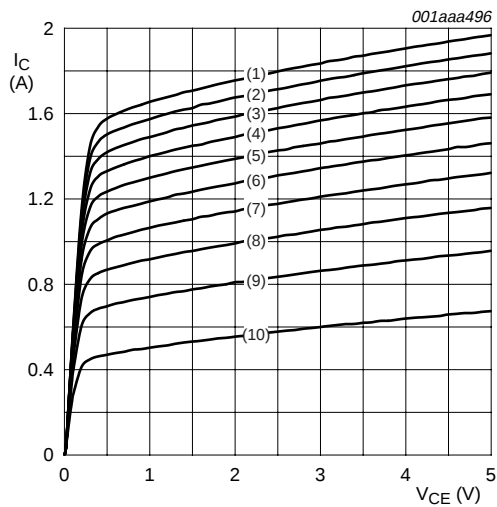
$I_C/I_B = 20$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig 9. Base-emitter saturation voltage as a function of collector current; typical values.



$I_C/I_B = 50$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

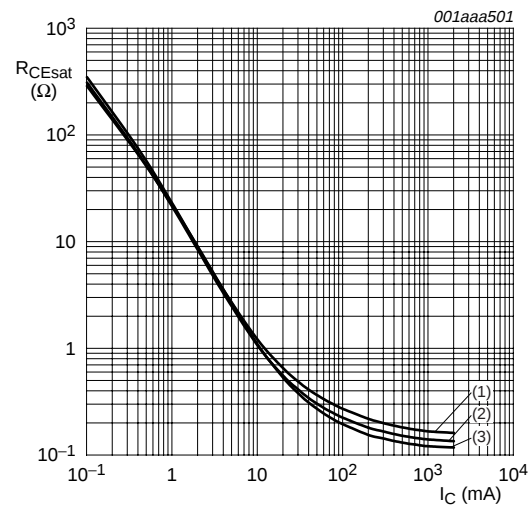
Fig 10. Base-emitter saturation voltage as a function of collector current; typical values.



$T_{amb} = 25\text{ }^{\circ}\text{C}$.

- (1) $I_B = 35\text{ mA}$.
- (2) $I_B = 31.5\text{ mA}$.
- (3) $I_B = 28\text{ mA}$.
- (4) $I_B = 24.5\text{ mA}$.
- (5) $I_B = 21\text{ mA}$.
- (6) $I_B = 17.5\text{ mA}$.
- (7) $I_B = 14\text{ mA}$.
- (8) $I_B = 10.5\text{ mA}$.
- (9) $I_B = 7\text{ mA}$.
- (10) $I_B = 3.5\text{ mA}$.

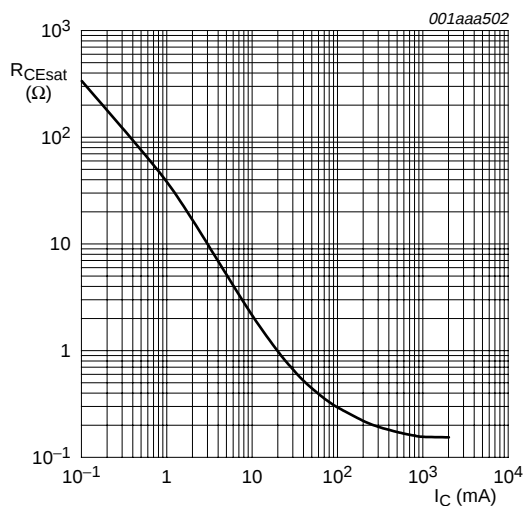
Fig 11. Collector current as a function of collector-emitter voltage; typical values.



$I_C/I_B = 10$.

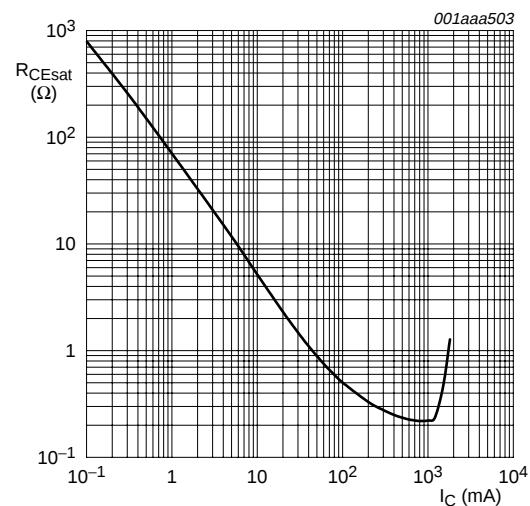
- (1) $T_{amb} = 100\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$.

Fig 12. Equivalent on-resistance as a function of collector current; typical values.



$I_C/I_B = 20$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig 13. Equivalent on-resistance as a function of collector current; typical values.



$I_C/I_B = 50$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig 14. Equivalent on-resistance as a function of collector current; typical values.

8. Package outline

Plastic surface mounted package; 6 leads

SOT457

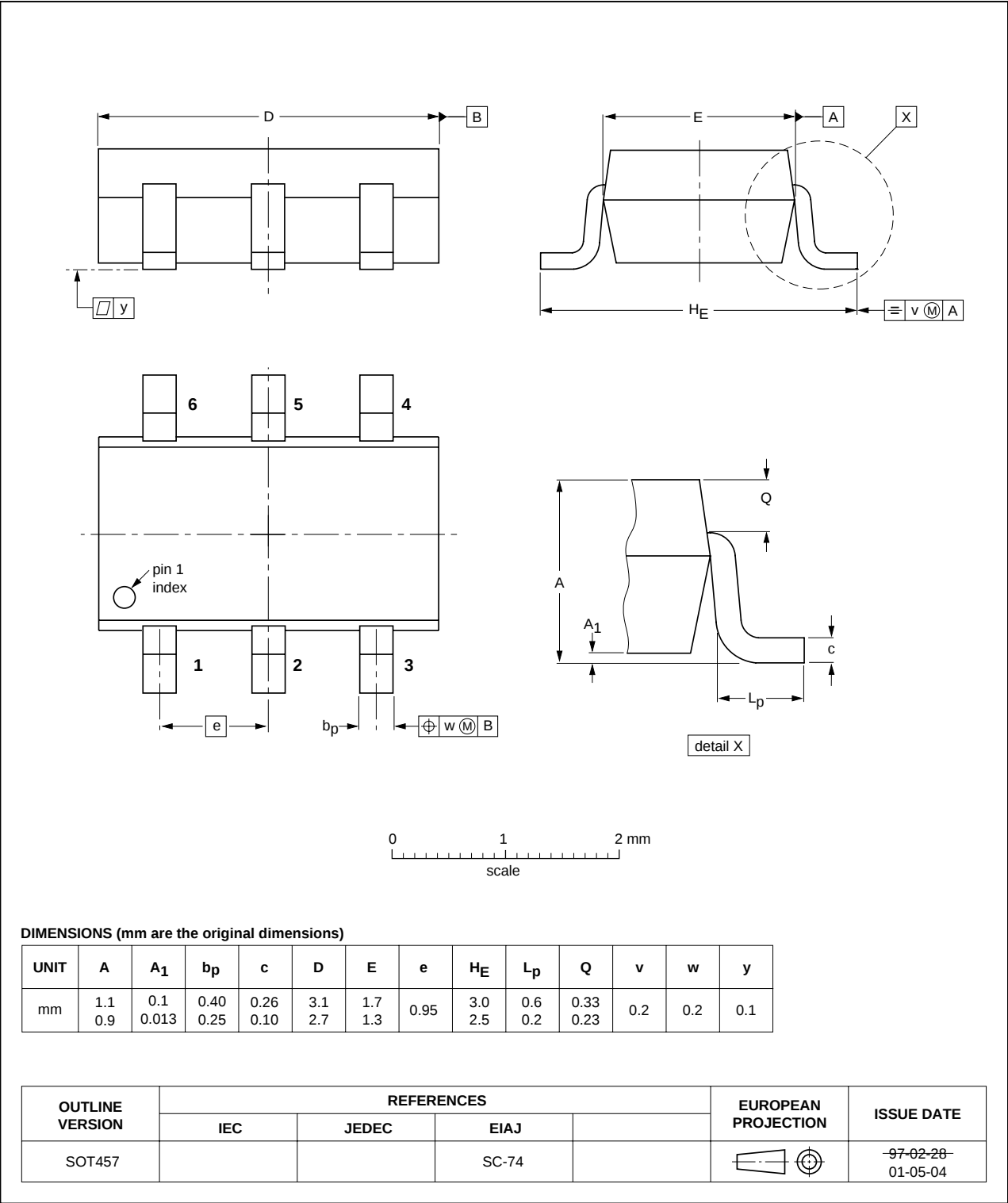


Fig 15. Package outline.

9. Revision history

Table 8: Revision history

Document ID	Release date	Data sheet status	Change notice	Order number	Supersedes
PBSS8110D_1	20040423	Product data	-	9397 750 12566	-

10. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2] [3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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